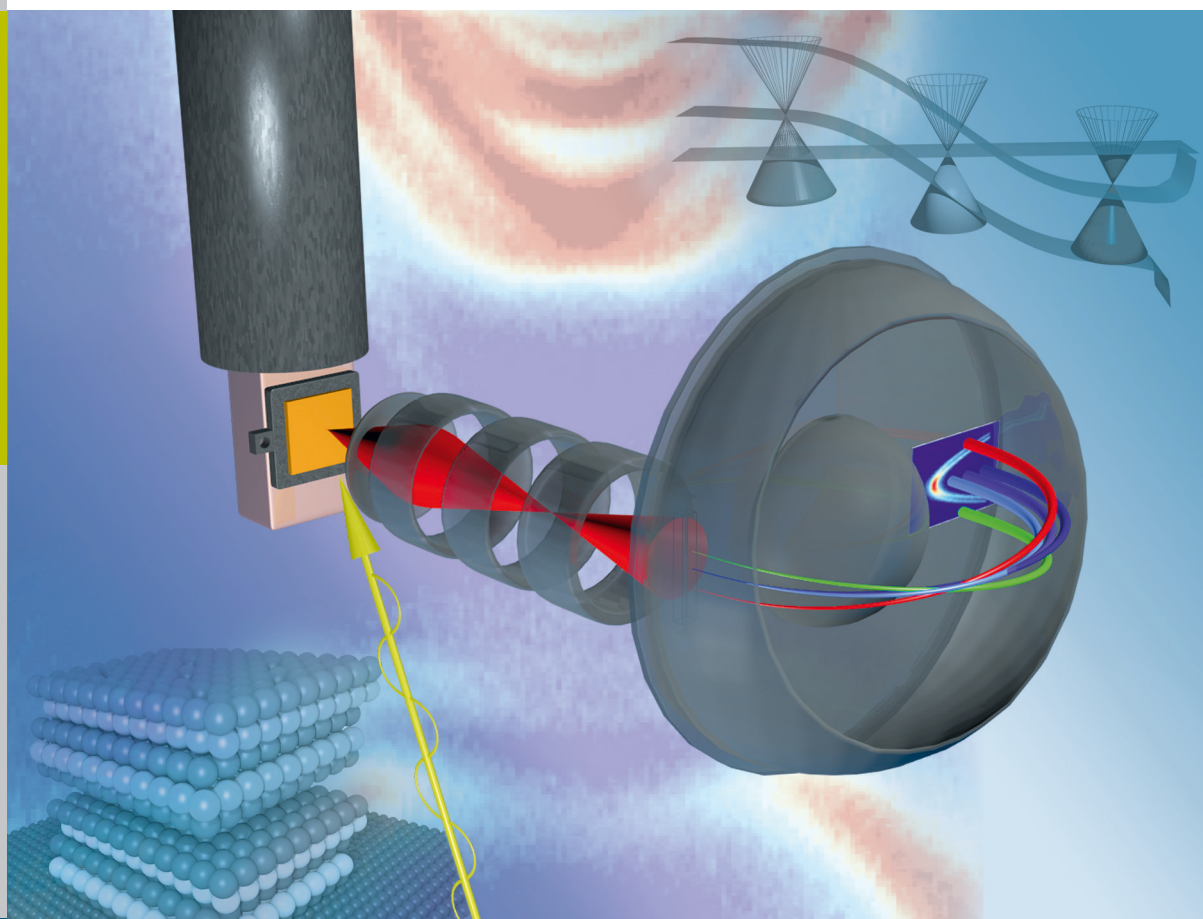


Band Structure Engineering in 3D Topological Insulators Investigated by Angle-Resolved Photoemission Spectroscopy

Markus Eschbach



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